

Designing Vertical Processors in Monolithic 3D

Bhargava Gopireddy, Josep Torrellas

University of Illinois at Urbana-Champaign

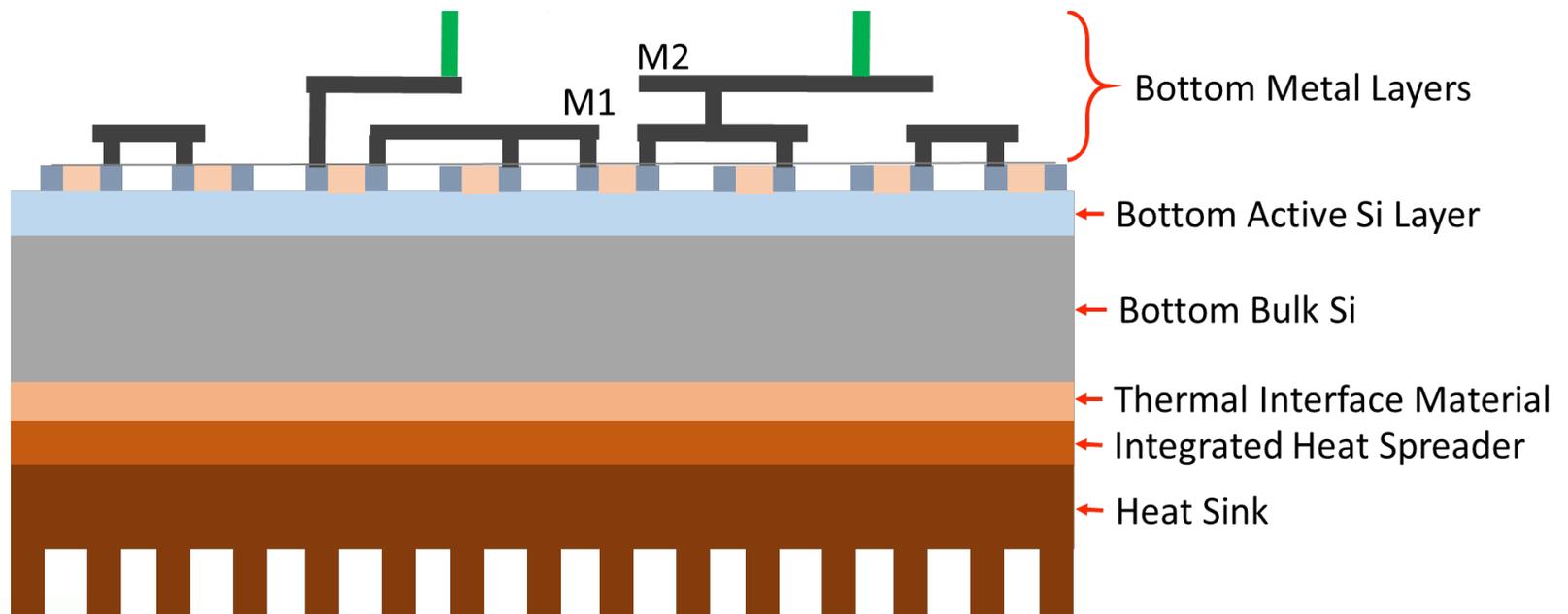
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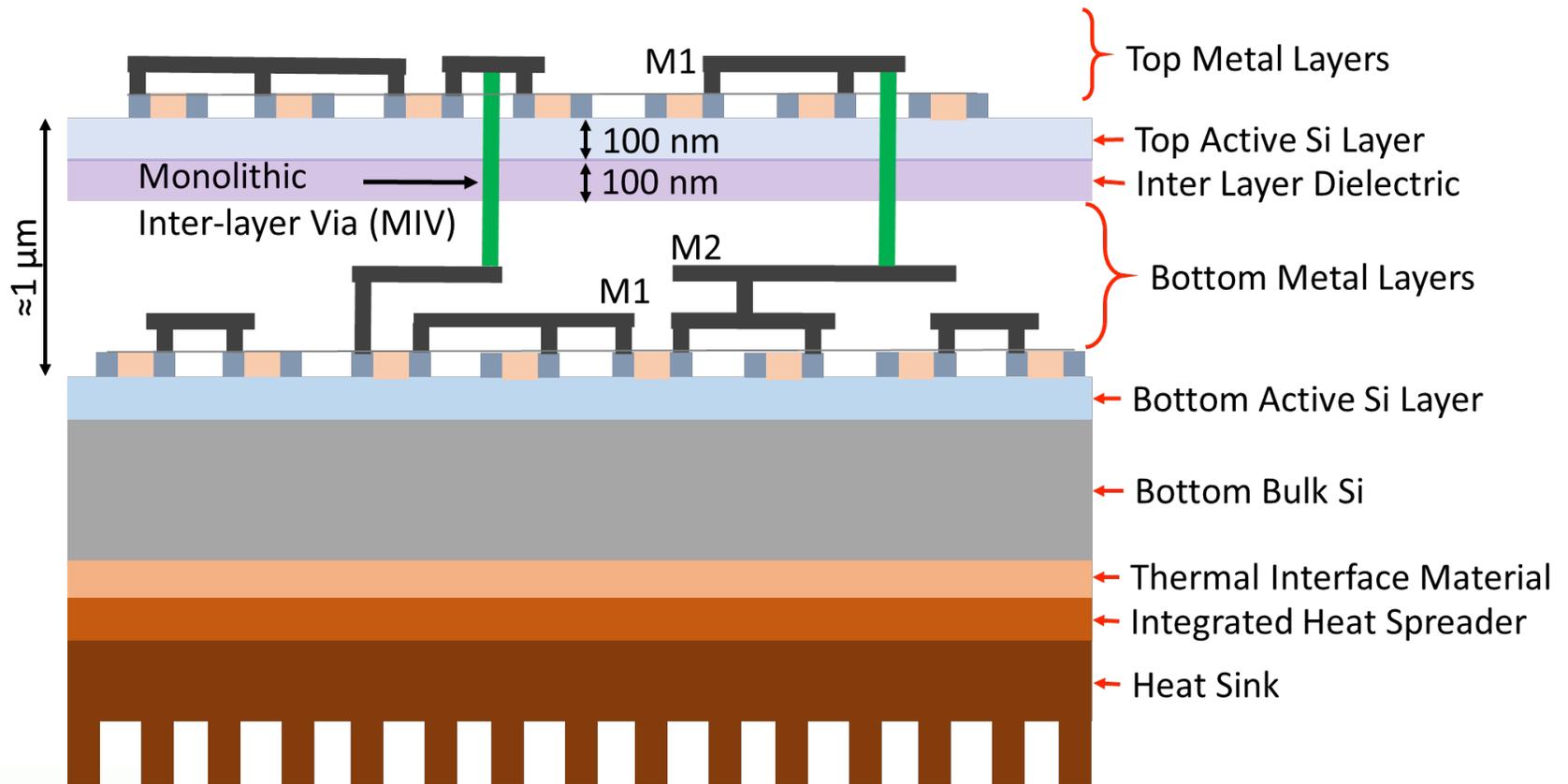
What is Monolithic 3D (M3D) ?

- Fabrication method that sequentially grows one or more Si layers on top of a base layer
 - As opposed to TSV based 3D stacking (TSV3D), that bonds pre-fabricated dies together



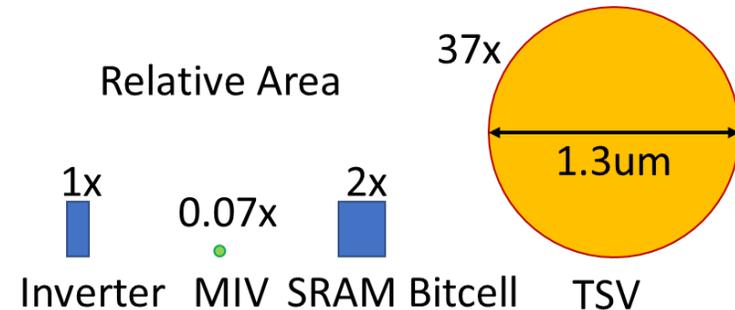
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Monolithic 3D vs TSV based 3D Stacking (TSV3D)

- Monolithic Inter-layer Via (MIV) diameter is much smaller
 - Diameter: 50 nm (MIV) vs 1.3 μm (TSV)
- Layers are close to each other
 - Better vertical thermal conduction



- ✓ Fine-grained integration
- ✓ High bandwidth and low latency
- ✓ Good vertical thermal conduction

Challenges of Monolithic 3D Integration

- Manufacturing the top layer without compromising the base layer
 - Conventional approach: High temperature steps in top layer fabrication
 - This hurts the bottom layer (metal and active silicon)

- Alternative: Use lower temperature process for the top layer

✓ Doesn't hurt the bottom layer
✗ Performance degradation in top layer

Contribution: Designing Vertical Processors in Monolithic 3D

- Design vertical cores by partitioning the pipeline stages into two layers
 - with and without top layer performance degradation
- First, partition the core assuming no slowdown in top layer
- Next, mitigate the impact of the top layer slowdown
 - **Critical Path Aware Partitioning** for logic and storage stages.
- Our evaluation shows an M3D core can significantly improve performance over a 2D or TSV3D design while reducing energy consumption

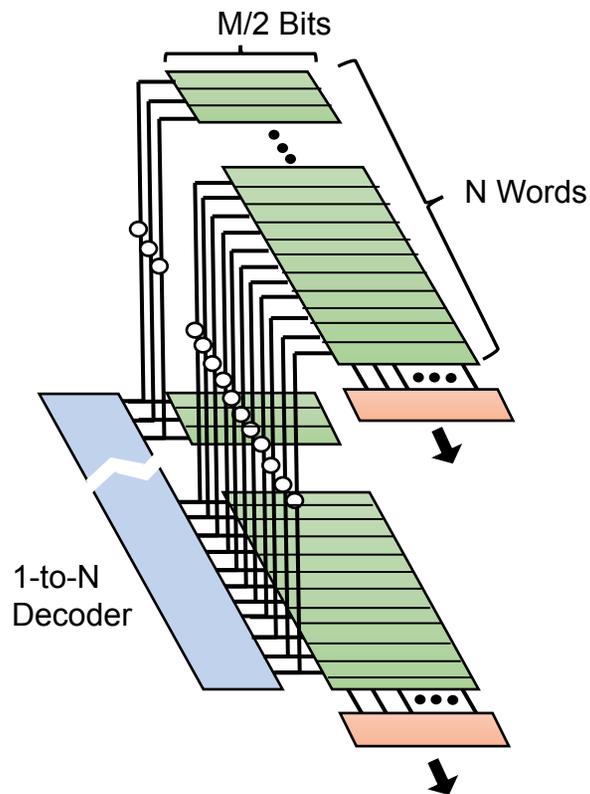
Partitioning Storage Stages in M3D

- SRAM/CAM structures within the core:
 - *Multi-ported*: Register File, Register Alias Table, Issue Queue etc.
 - *Single-ported*: Branch predictors, BTB, L1/L2 etc.

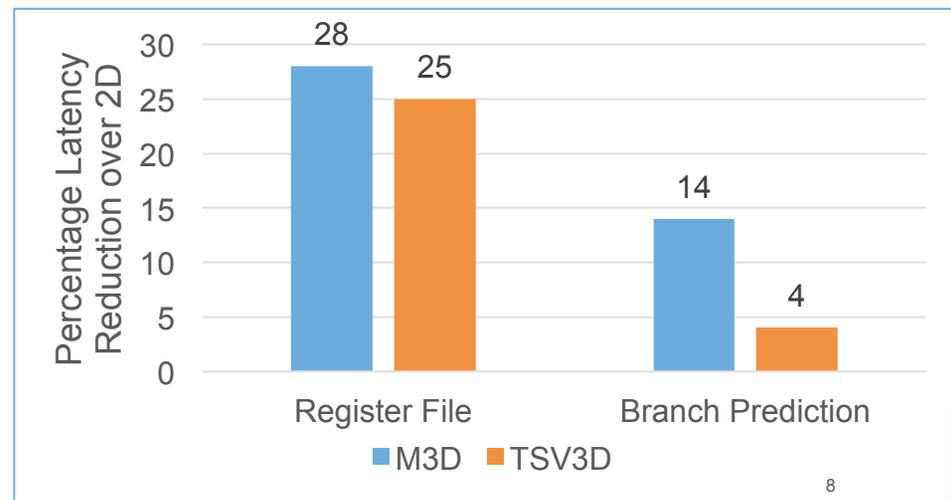
- 3D SRAM/CAM array partitioning schemes [1]
 - Bit Partitioning
 - Word Partitioning
 - Port Partitioning



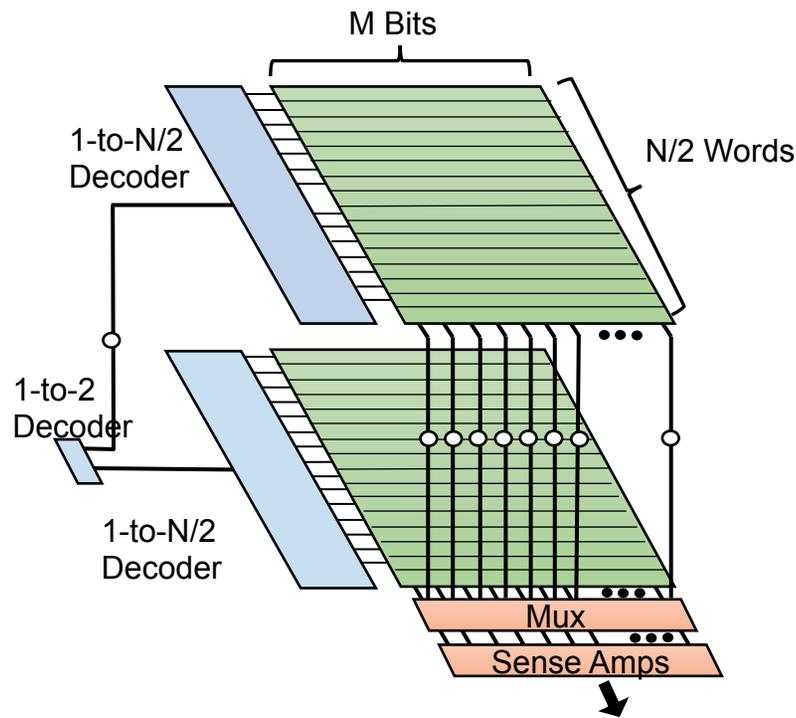
Bit Partitioning



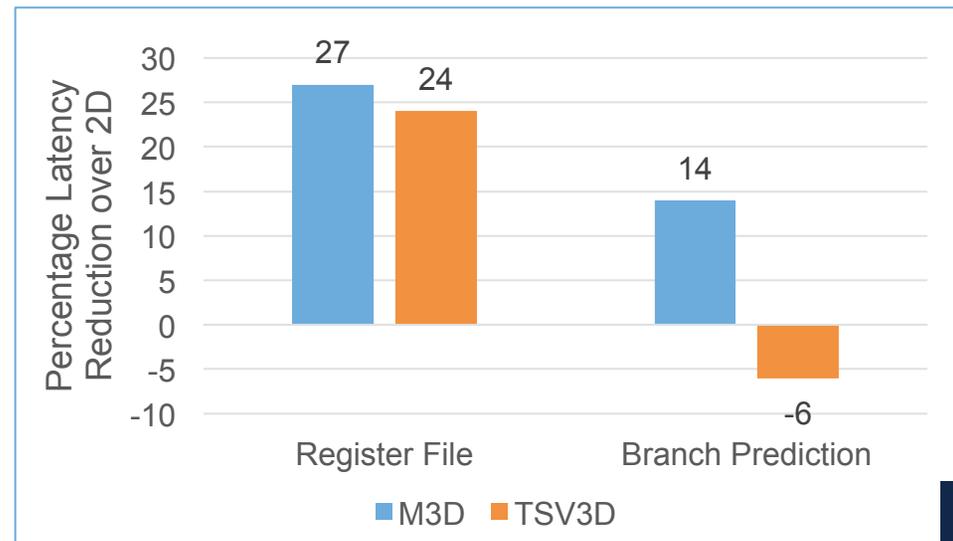
- Distribute half the bits of every word in each layer
- Each word requires an inter-layer via
- Multiported structure (e.g. Register File):
 - Bigger bitcells → higher gains
- Singleported structure (e.g. Branch Predictor):
 - Smaller bitcells → lower gains



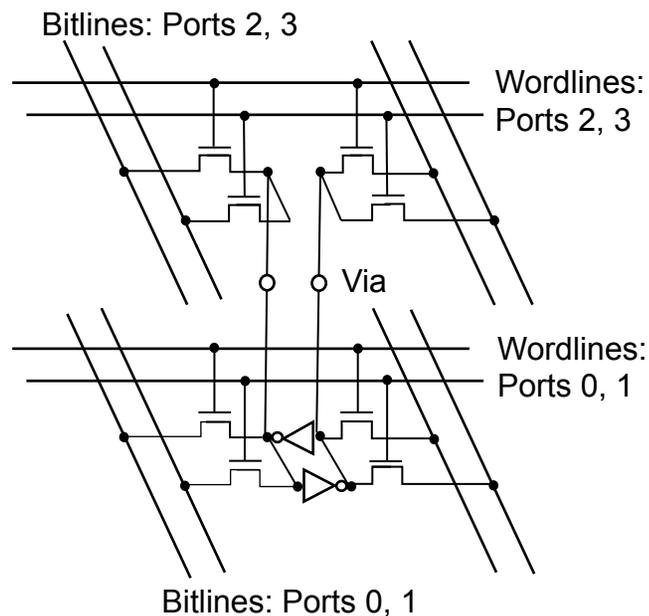
Word Partitioning



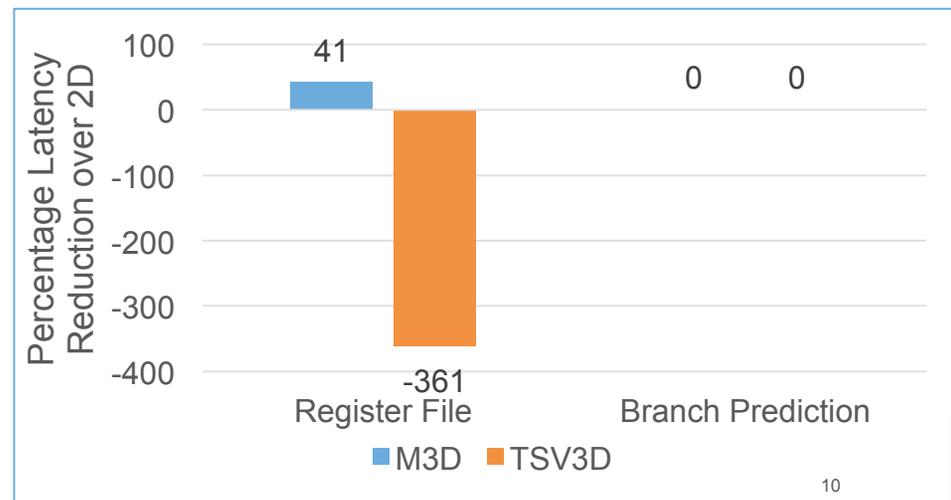
- Distribute half of the words in each layer
- Requires one inter-layer via per bit
- Similar behavior as Bit partitioning



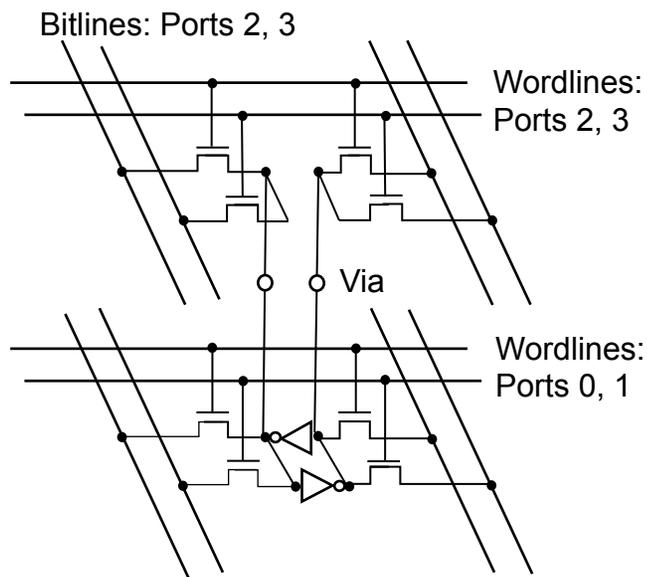
Port Partitioning



- Distribute half the ports in each layer
- Quadratic reduction in area footprint
- Two vias per bitcell
- Applicable only for multiported structures
- TSVs simply have too much area overhead

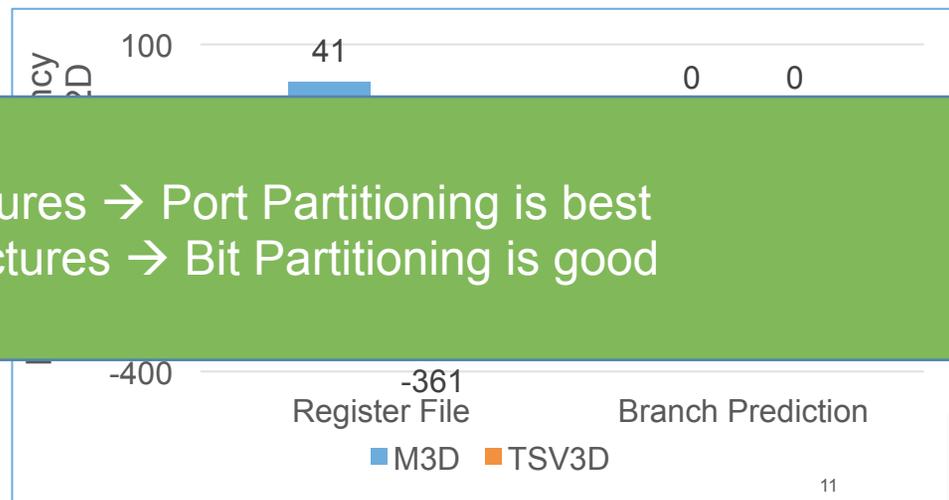


Port Partitioning



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Multiported structures → Port Partitioning is best
 Singleported structures → Bit Partitioning is good



Partitioning Logic Stages in M3D

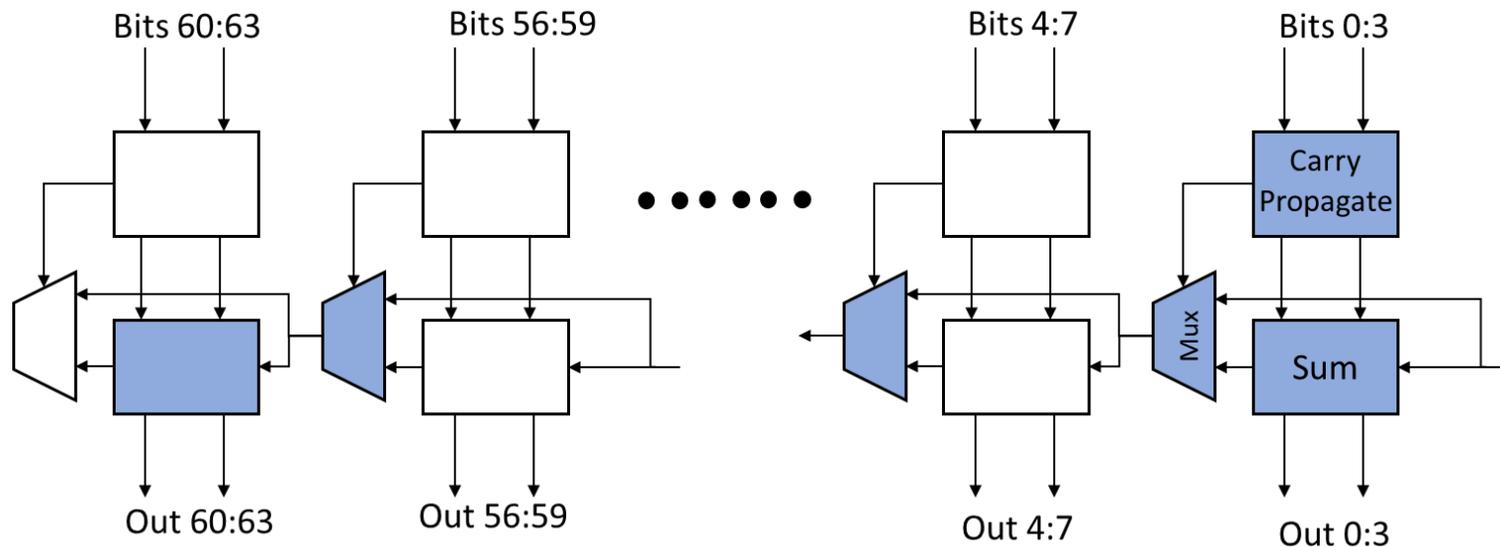
- Benefit: Reduction in wire delay
- Semi-global wires are significantly shorter
 - Critical paths within a core such as **load-to-use, branch misprediction, ALU+Bypass** are shorter
 - Improves both core frequency and IPC

Hetero Layer Partitioning (M3D-Hetero)

- Low temperature processing → performance degradation in the top layer
 - Top layer inverter delay: 17% lower
 - Overall frequency: 9% lower
- Propose: Mitigate the impact through **Critical Path Aware Partitioning**

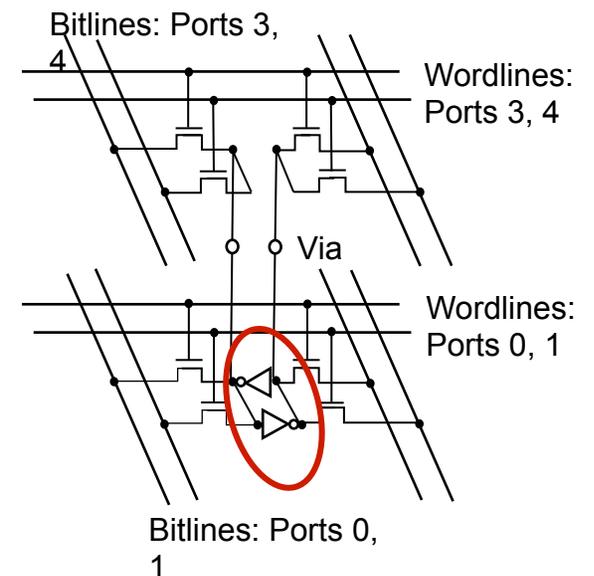
M3D-Hetero Logic Stages: Execution Unit

- ALU has many paths that are not critical to stage delay
 - For example, in a carry skip adder, only shaded parts are critical.
 - Propose: Place the critical paths in bottom layer ; rest in the top layer



M3D-Hetero Storage Structures

- Port Partitioned Structures:
 - Area slack exists in top layer, as the bitcell is only in the bottom layer
 - Propose: *Asymmetric Port Partitioning*
 - Increase the size of access transistors in the top layer (for speed)
 - Place more ports in bottom layer than in top layer



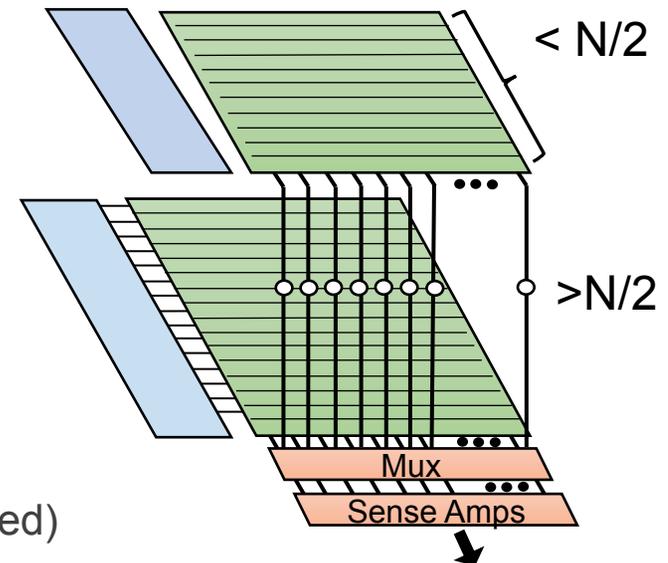
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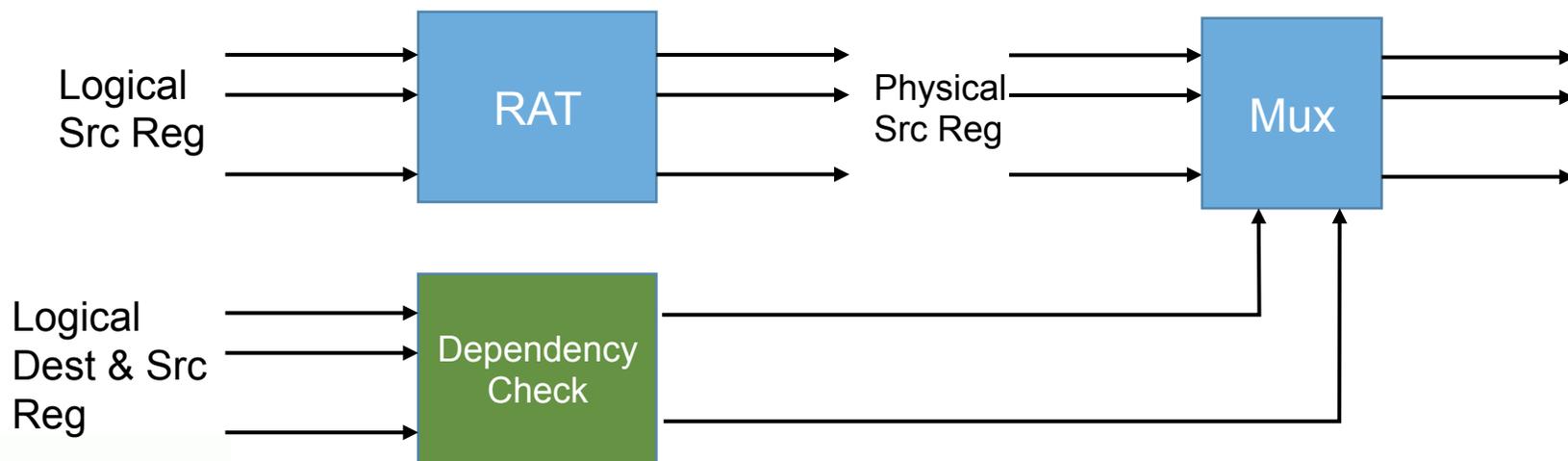
- Bit/Word Partitioned Structures:

- Propose: *Asymmetric Array Partitioning*
 - Asymmetrically partition bits/words across layers
 - Assign smaller section to the top layer
 - Increase the size of transistors in top layer (for speed)



M3D-Hetero Stages with both Logic and SRAM Structures

- Rename consists of Register Alias Table (RAT) and other logic:
 - Register Alias Table (multi-ported) → Perform asymmetric port partitioning
 - Dependency check → Place in top layer (Not critical)
 - Shadow RAT tables → Place in top layer (Not critical)
 - Decoder to RAT and peripheral logic → Place in bottom layer (Critical)



Summary: Hetero Layer Partitioning in M3D

Stage Type	Mitigation Technique	
Logic Stages	Critical paths in bottom layer; non-critical paths in top	
Storage Stages	Port Partitioning	Asymmetric partitioning of ports; and larger access transistors in top layer
	Bit/Word Partitioning	Asymmetric partitioning of array; and larger bitcells in top layer
Mixed Stages	Combination of above techniques	

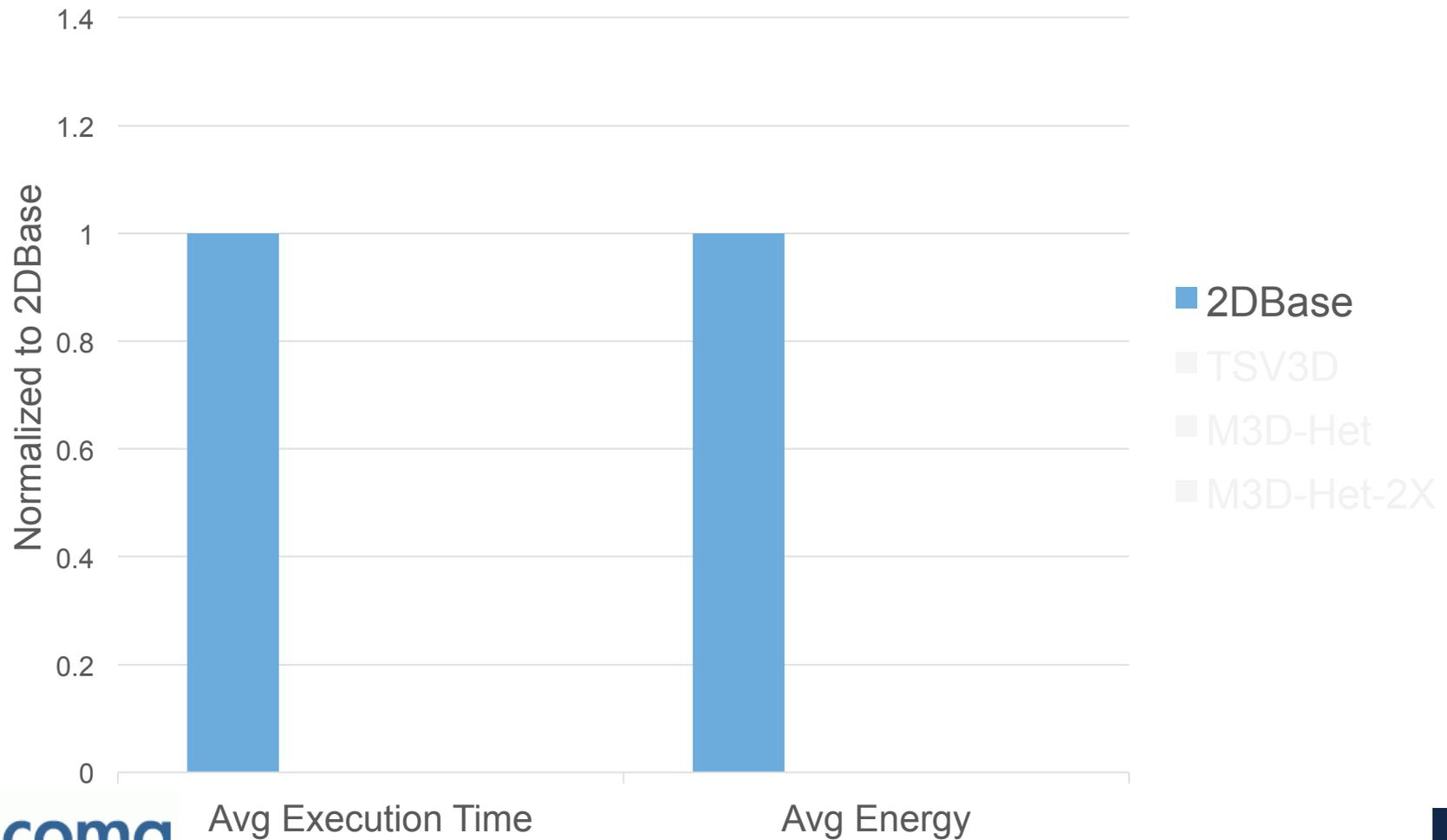
How to Exploit Stage Delay Reduction in M3D ?

- ✓ Increase frequency
- ✓ Increase the size or the number of ports for key structures
 - Register File, Issue Queue etc.
 - Increase issue width at same frequency
- ✓ Keep the same frequency, but reduce the voltage
 - Operate more cores within the same power budget

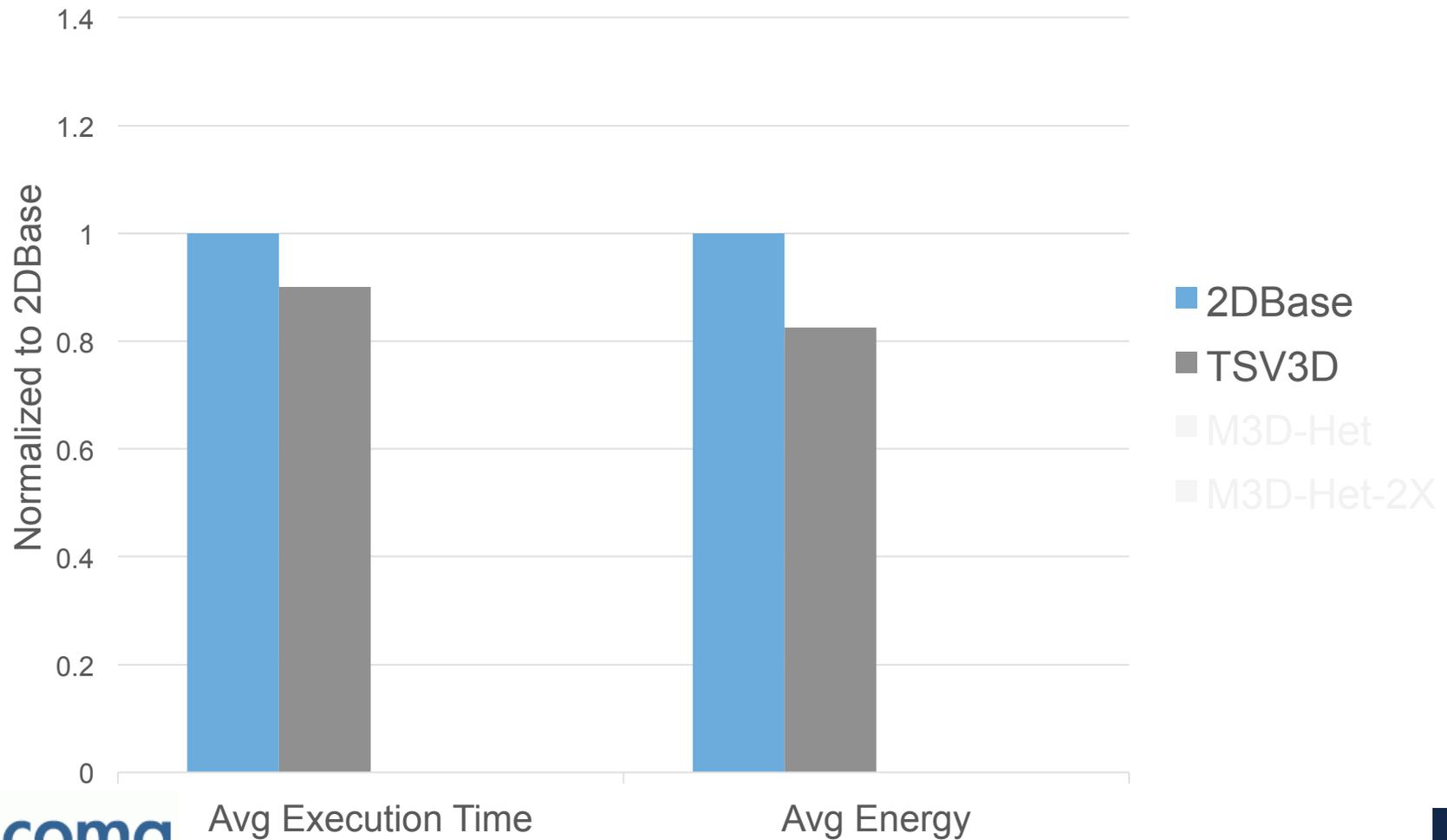
Evaluation: Configurations & Frequency

- *2D Base*: Four 6-wide OOO cores
 - Caches: DL1 & IL1 32KB ; L2 256 KB ; Entries: RF(160) ; ROB(192) ; IQ(84) ; LQ(72); SQ(56)
 - Frequency = 3.3 GHz
- *M3D-Het* : M3D with top layer slowdown and our modifications
 - Stage with lowest delay reduction: SQ/BPT at 13%
 - Frequency = 3.79 GHz
- *TSV3D*: Traditional TSV3D
 - Stage with lowest delay reduction: BTB at -6% (negative)
 - Frequency = 3.3 GHz
- *M3D-Het-2X*: Increase cores within same power budget
 - 2X as many cores at F = 3.3 GHz

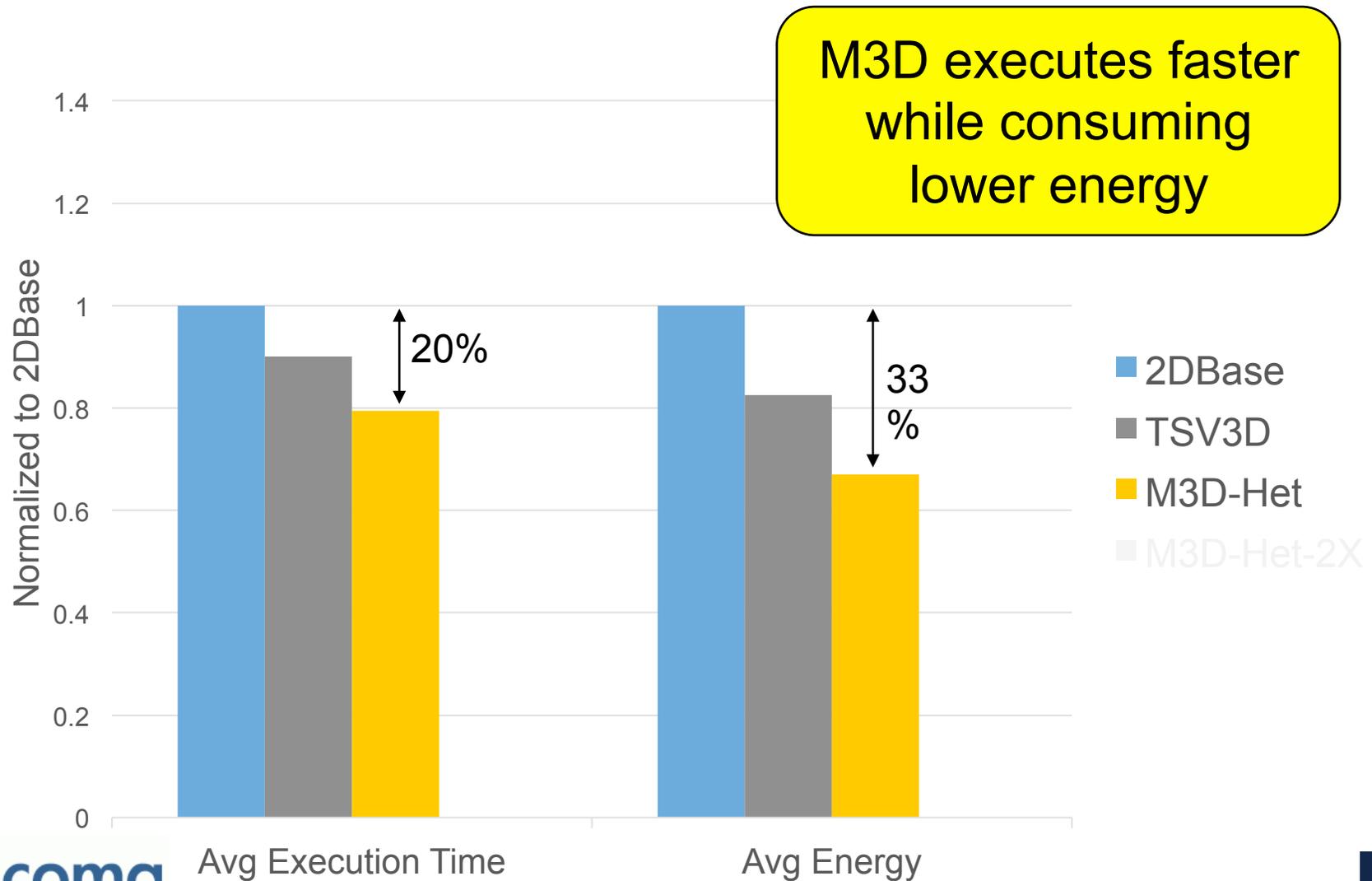
Evaluation of M3D Design Choices



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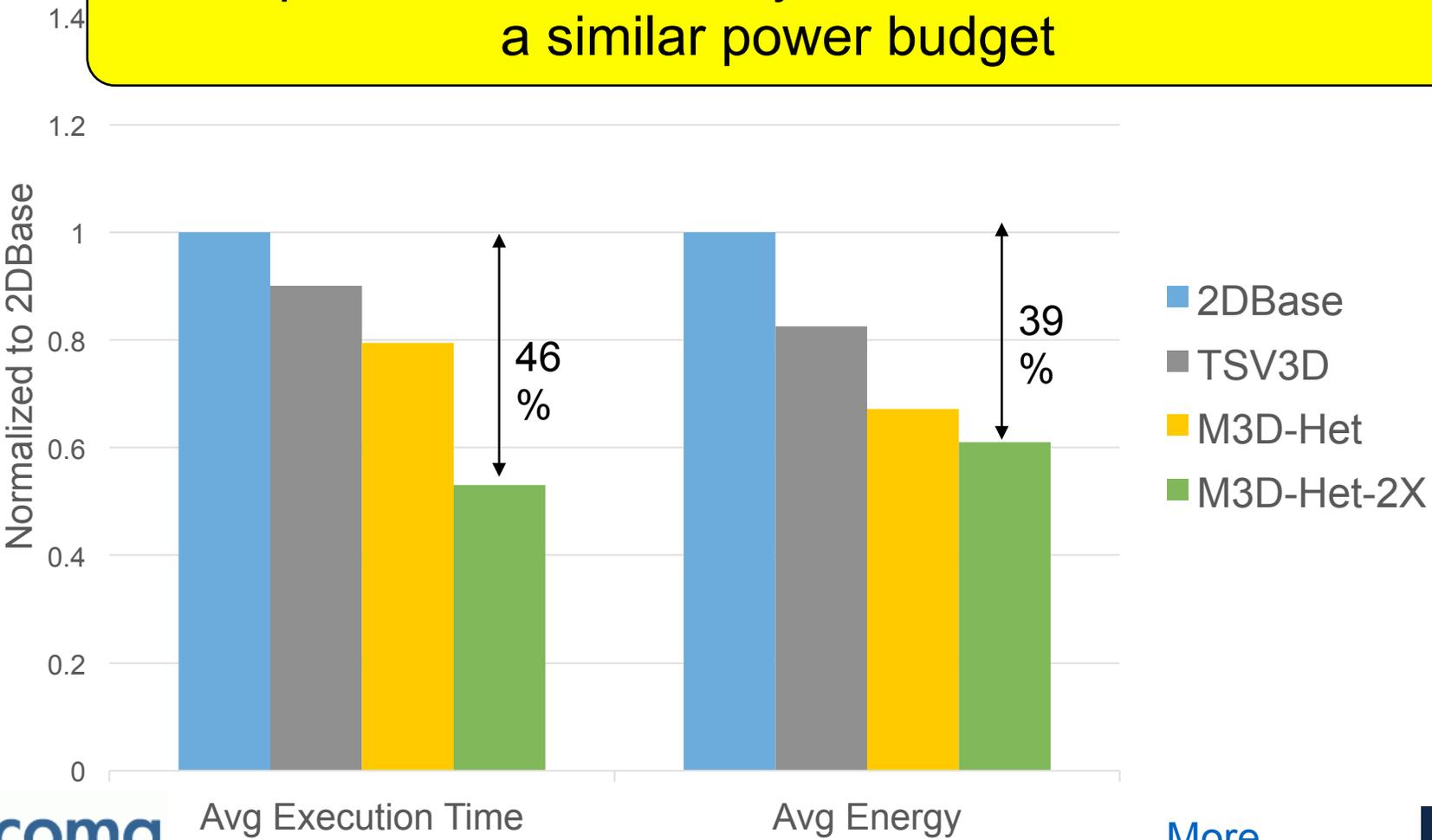


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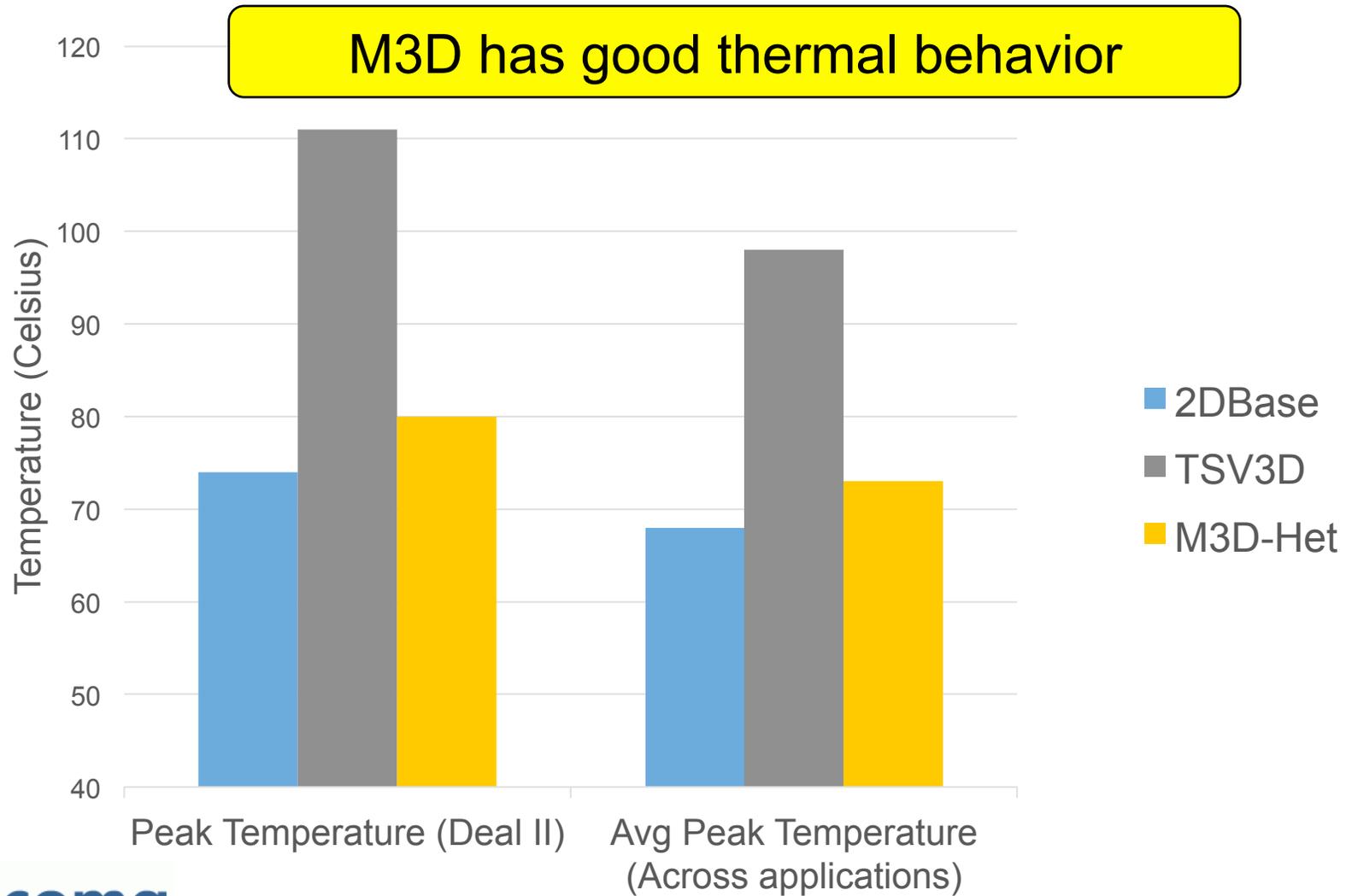


Evaluation of M3D Design Choices

Can operate twice as many M3D cores as 2DBase in a similar power budget



Thermal Behavior: Peak Temperature



Summary: Designing Vertical Processors in Monolithic 3D

- First work to partition a core in an M3D stack
- Proposed **Critical Path Aware Partitioning** strategies to mitigate the performance impact of a degraded top layer.
- Overall, M3D can operate twice as many cores as a 2D design within a similar power budget
 - Improves execution time by 46% while consuming 39% lower energy.

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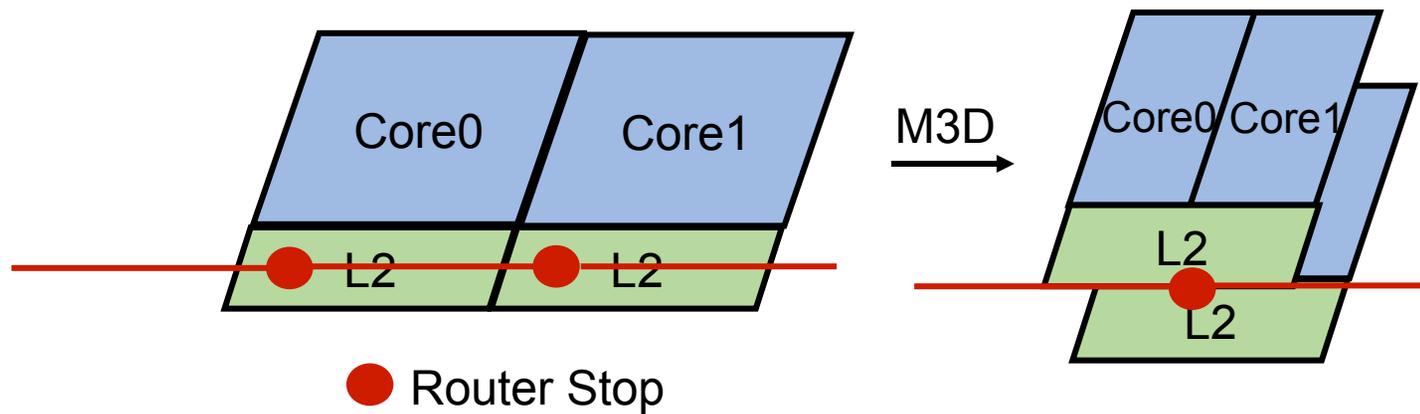
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Backup

Caches and NoC

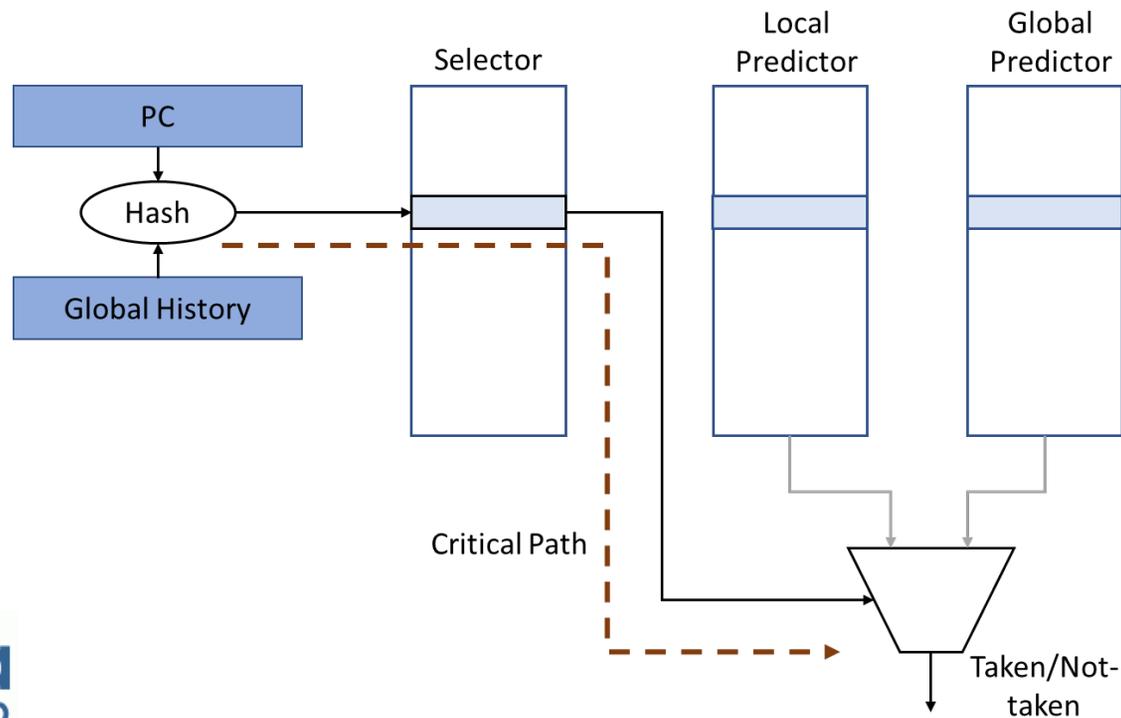
- Shared L2 Cache, and NoC Router Stop across two adjacent cores



Stages with Logic and SRAM Structures

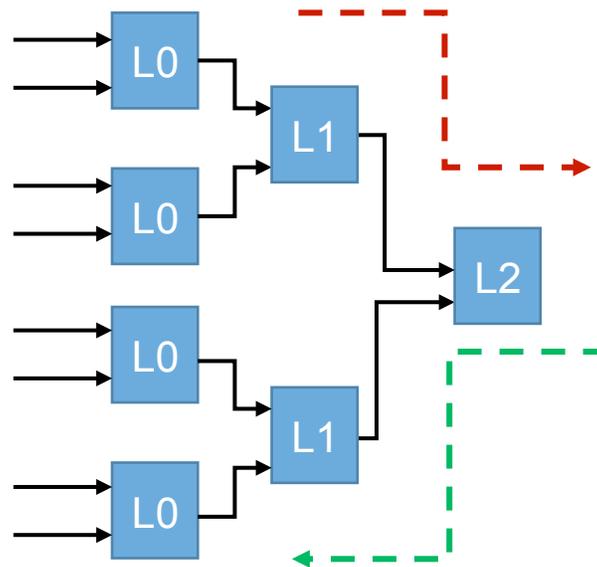
• Fetch and Branch Prediction:

- Consists of 4 parallel paths: Increment PC, RAS, BTB and Branch Prediction
- RAS, increment PC are non-critical and are in top tier
- BTB access and Branch Prediction are both critical and use asymmetric array partition



Stages with Logic and CAM Structures

- Issue Stage consists of Wakeup and Select logic:
 - Wakeup consists of IQ which is a CAM structure → Asymmetric port partitioning
 - Select consists of multi-level arbitration
 - Within each arbiter:
 - First phase: Request → critical and is in bottom layer
 - Second phase: Grant → has slack and is in top layer.



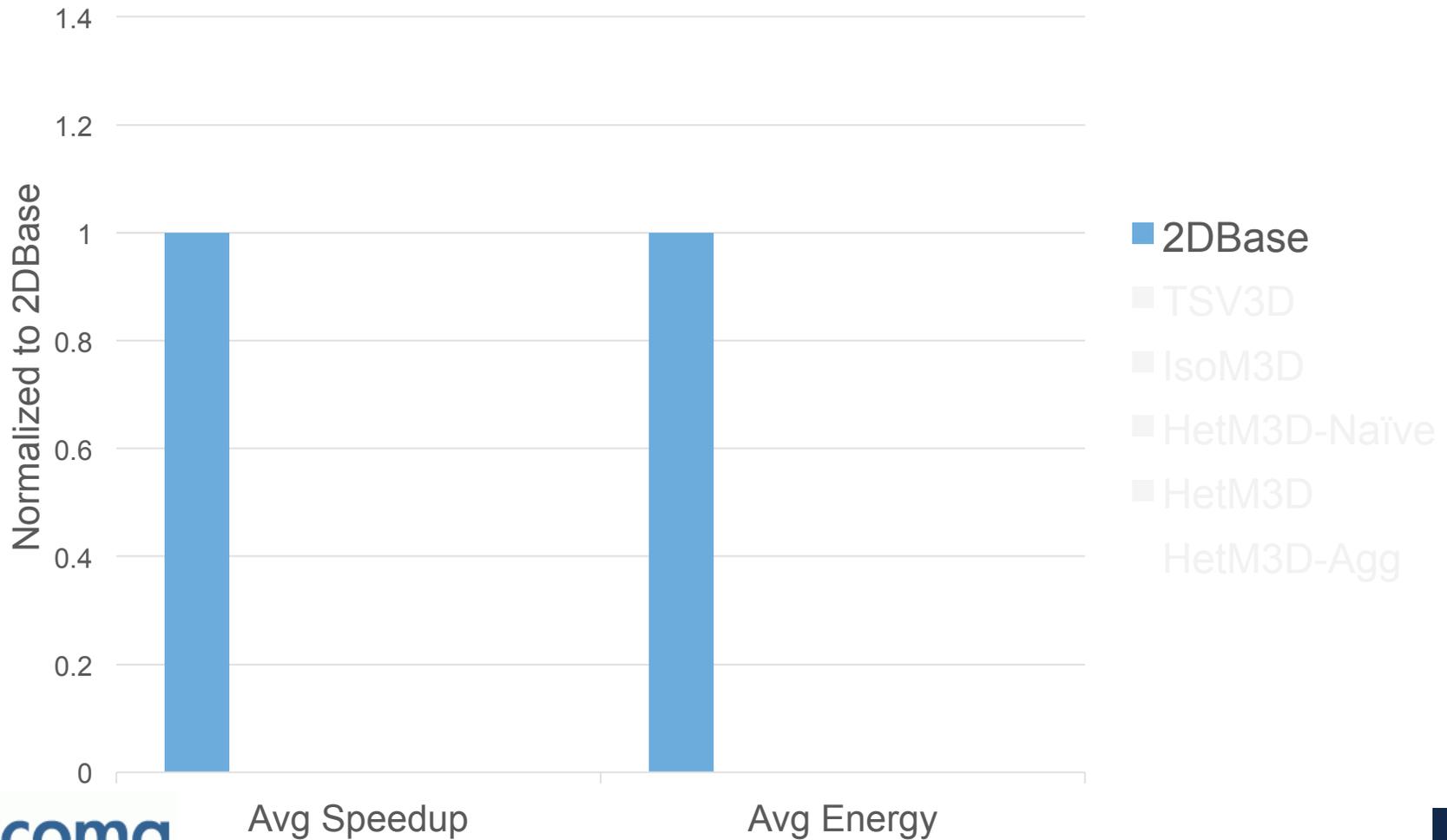
Stages with Logic and CAM Structures

- Load Store Unit:
 - Critical path: Store forwarding to a younger load, on a hit in Store Queue
 - Includes SQ access, Priority encoder and Store buffer access
 - LQ, SQ CAMs → Asymmetric Port partitioning
 - Priority encoder after SQ is placed in bottom layer.
 - Balance area between LQ/SQ across layers.

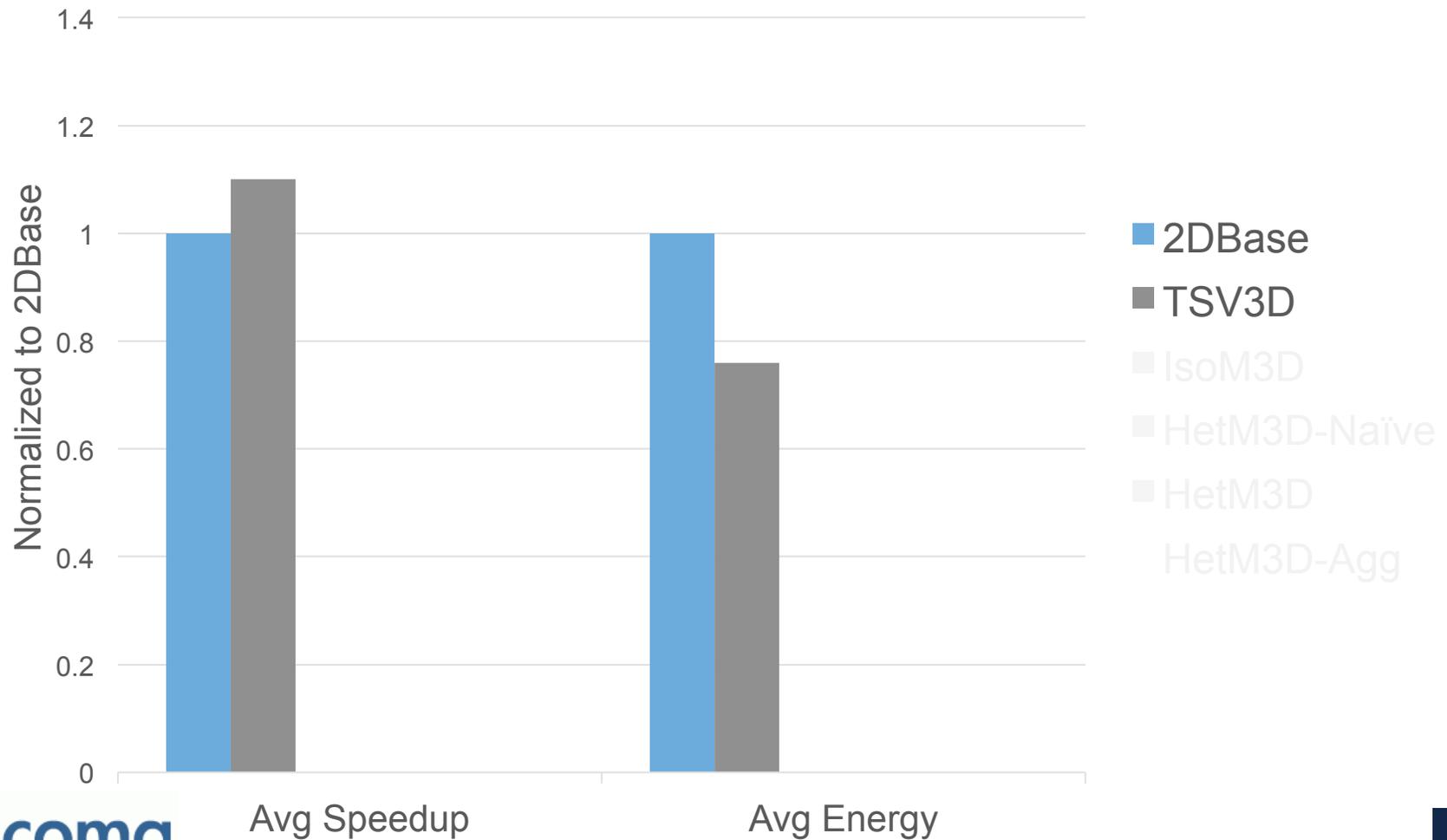
Evaluation: Frequency of Operation for M3D

- *2D Base*: 6-wide OOO core
 - $F = 3.3$ GHz
- *IsoM3D*: M3D without top layer degradation:
 - Stage with least delay reduction: SQ/BPT at 14% $\rightarrow F = 3.83$ GHz
- *HetM3D–Naïve* : 9% lower frequency due to slow top layer
 - $F = 3.5$ GHz
- *HetM3D* : M3D with top layer slowdown and our modifications
 - Stage with least delay reduction: SQ/BPT at 13% $\rightarrow F = 3.76$ GHz
- *HetM3D–Agg*: An aggressive HetM3D with traditional frequency critical structures
 - IQ (24%) and ALU+Bypass (28%) are the only limiters $\rightarrow F = 4.34$ GHz

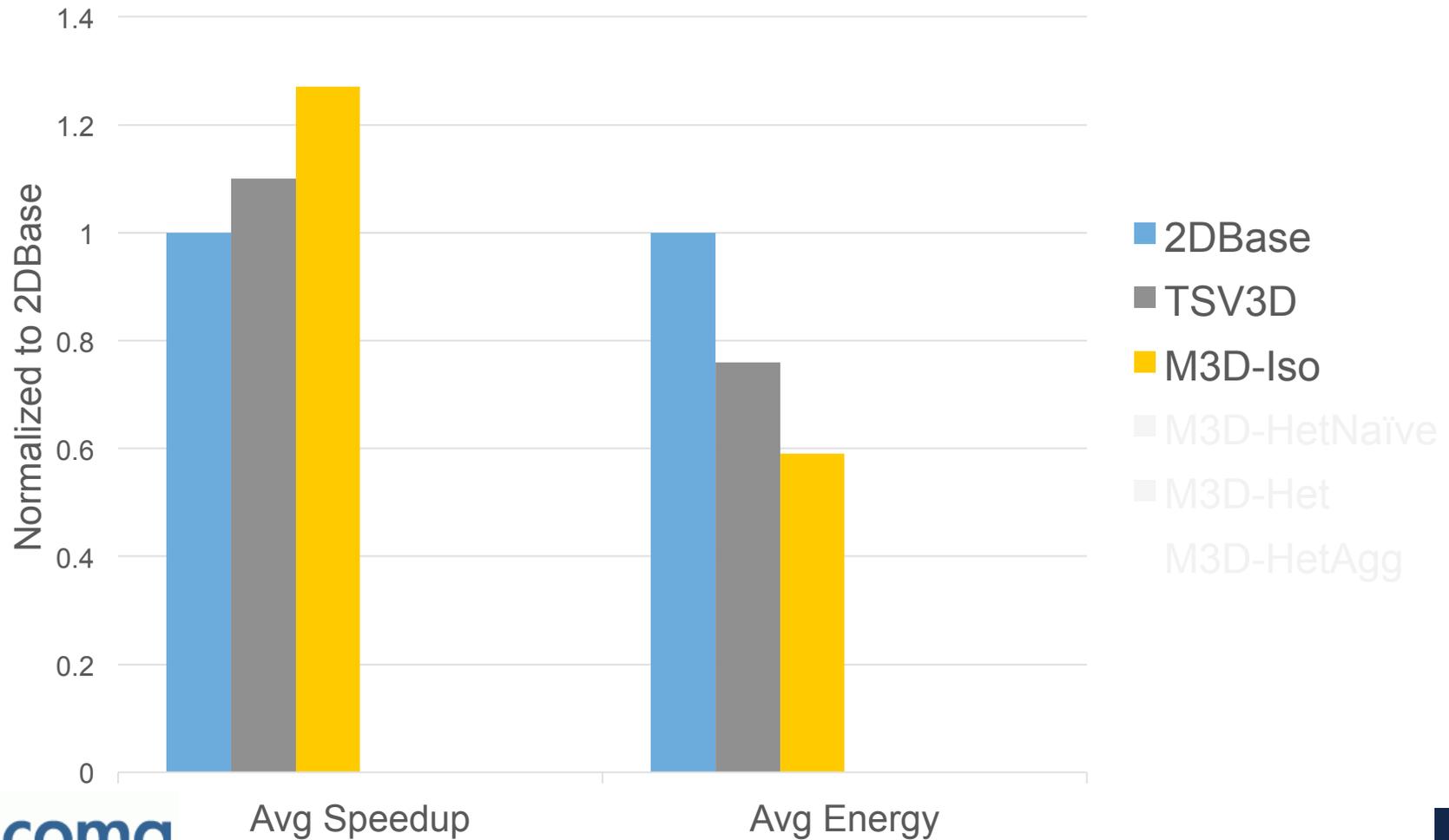
Single Thread Results: SPEC Benchmark Suite



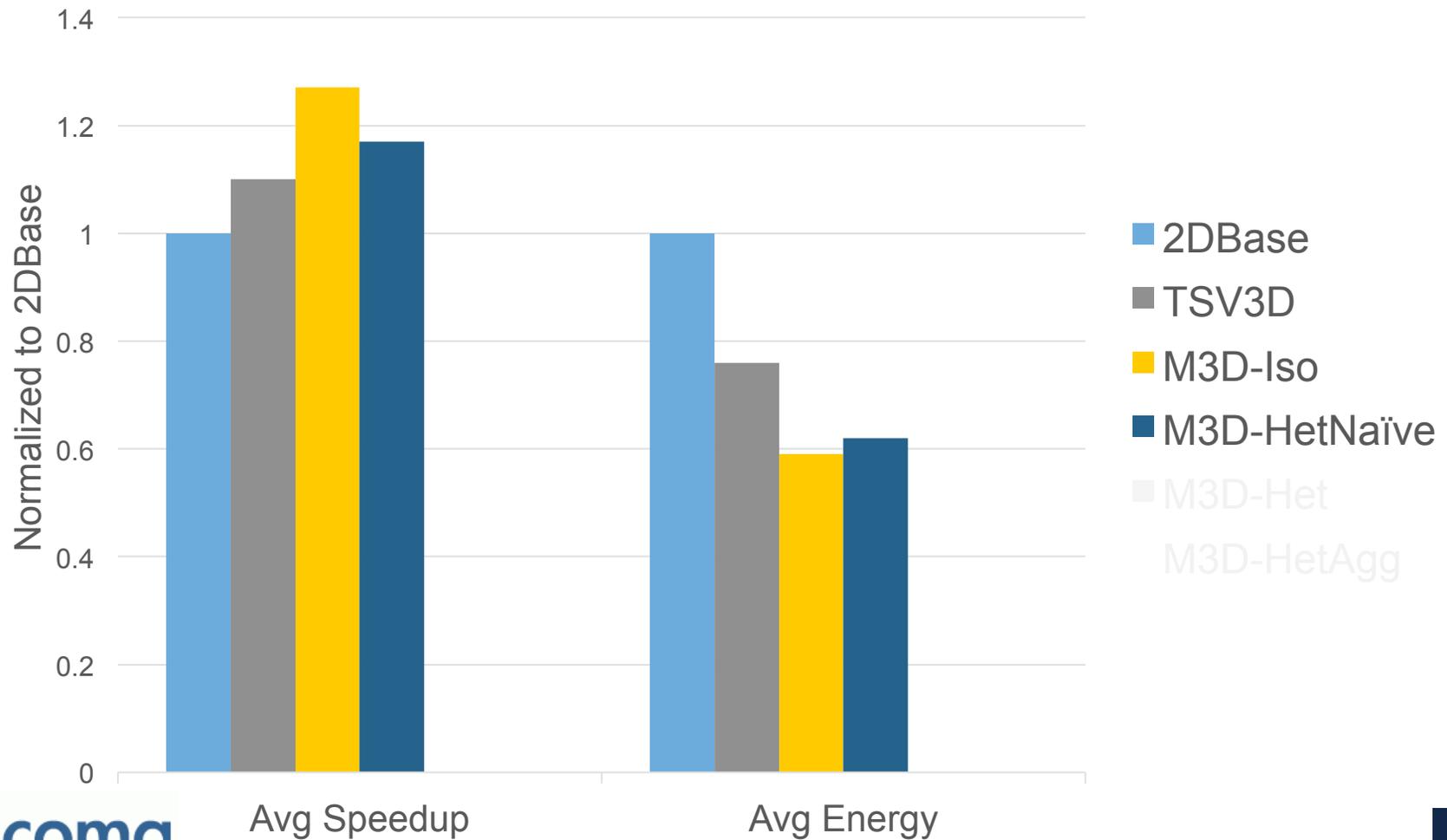
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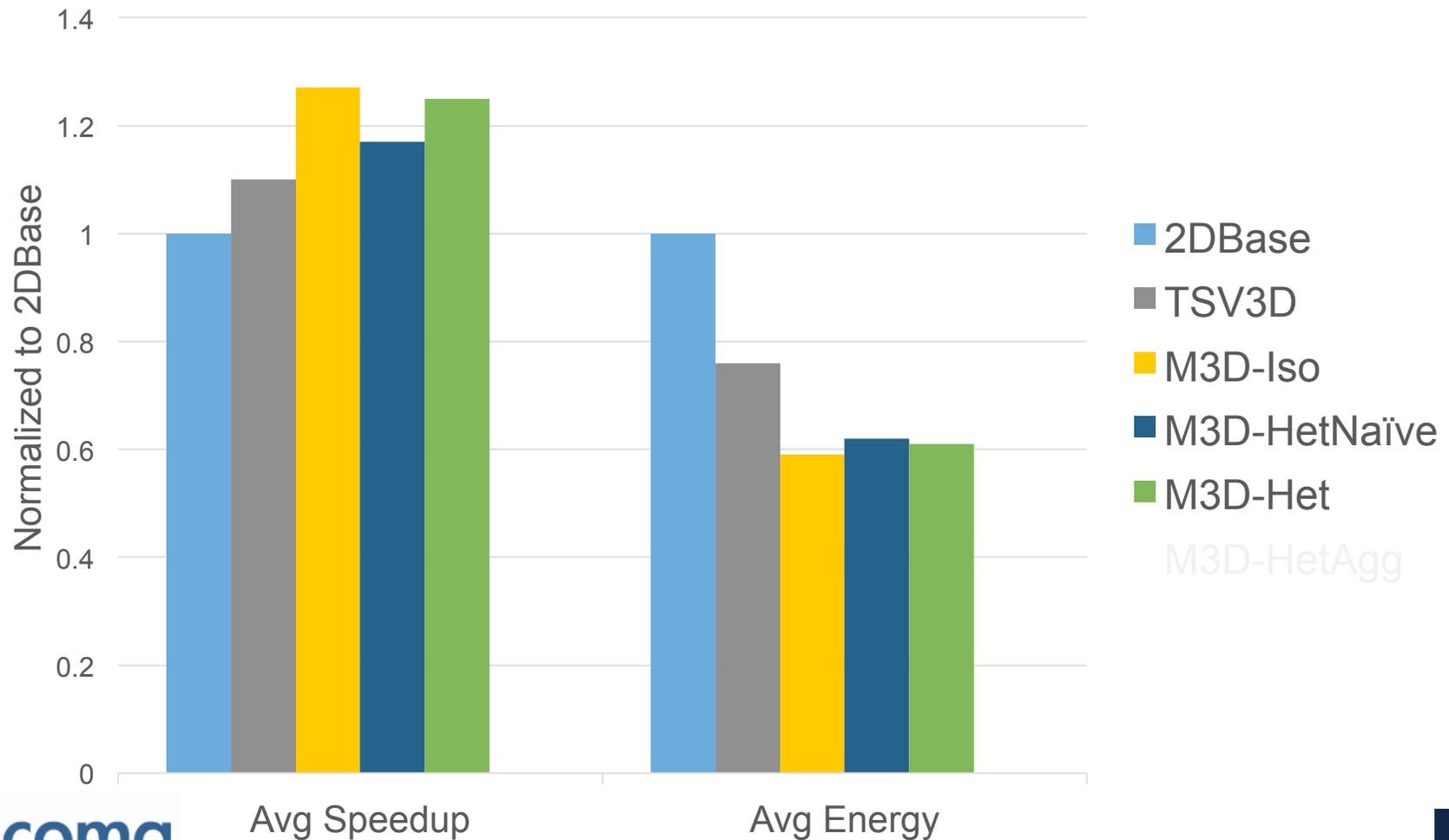
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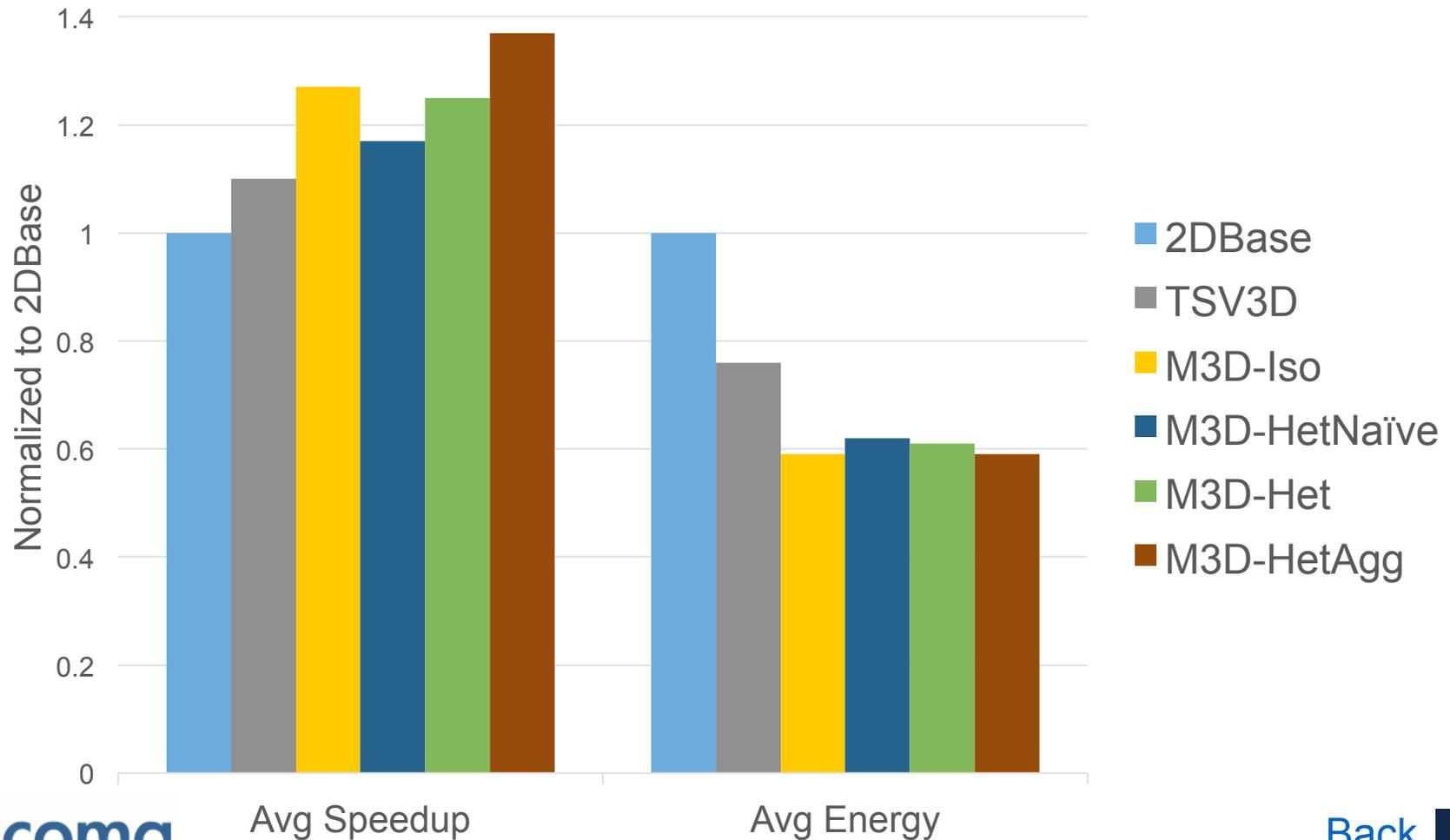
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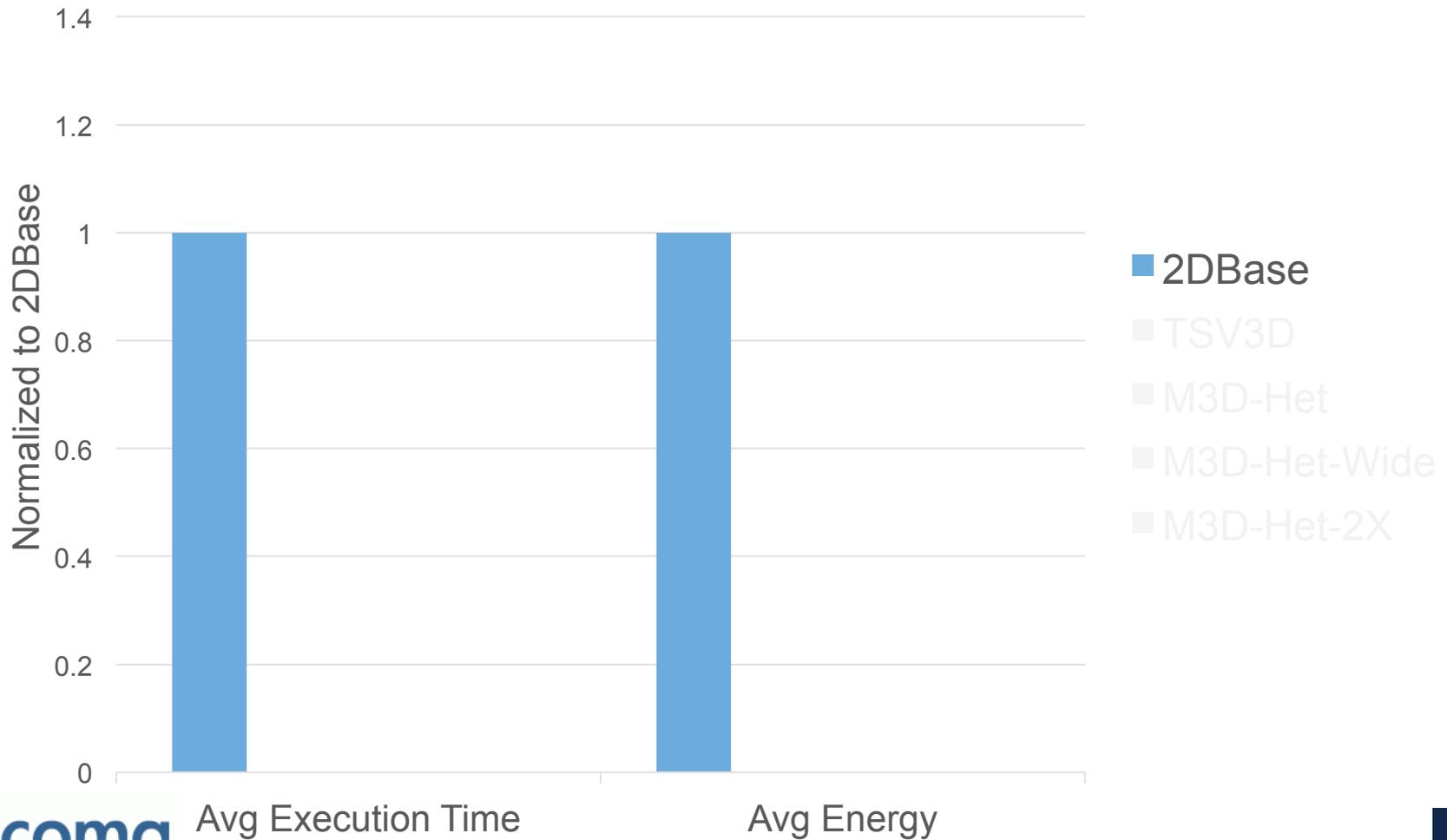
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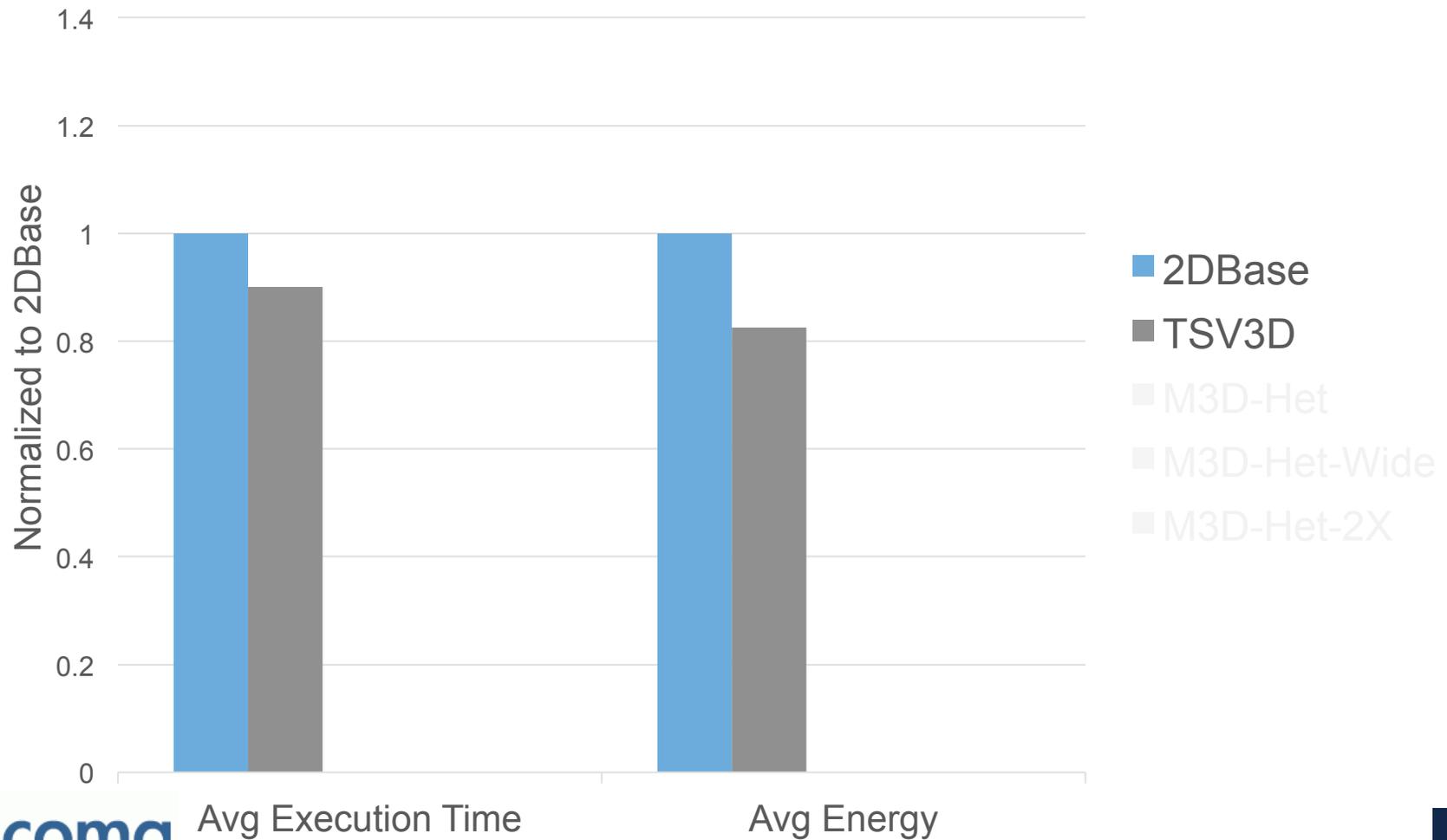
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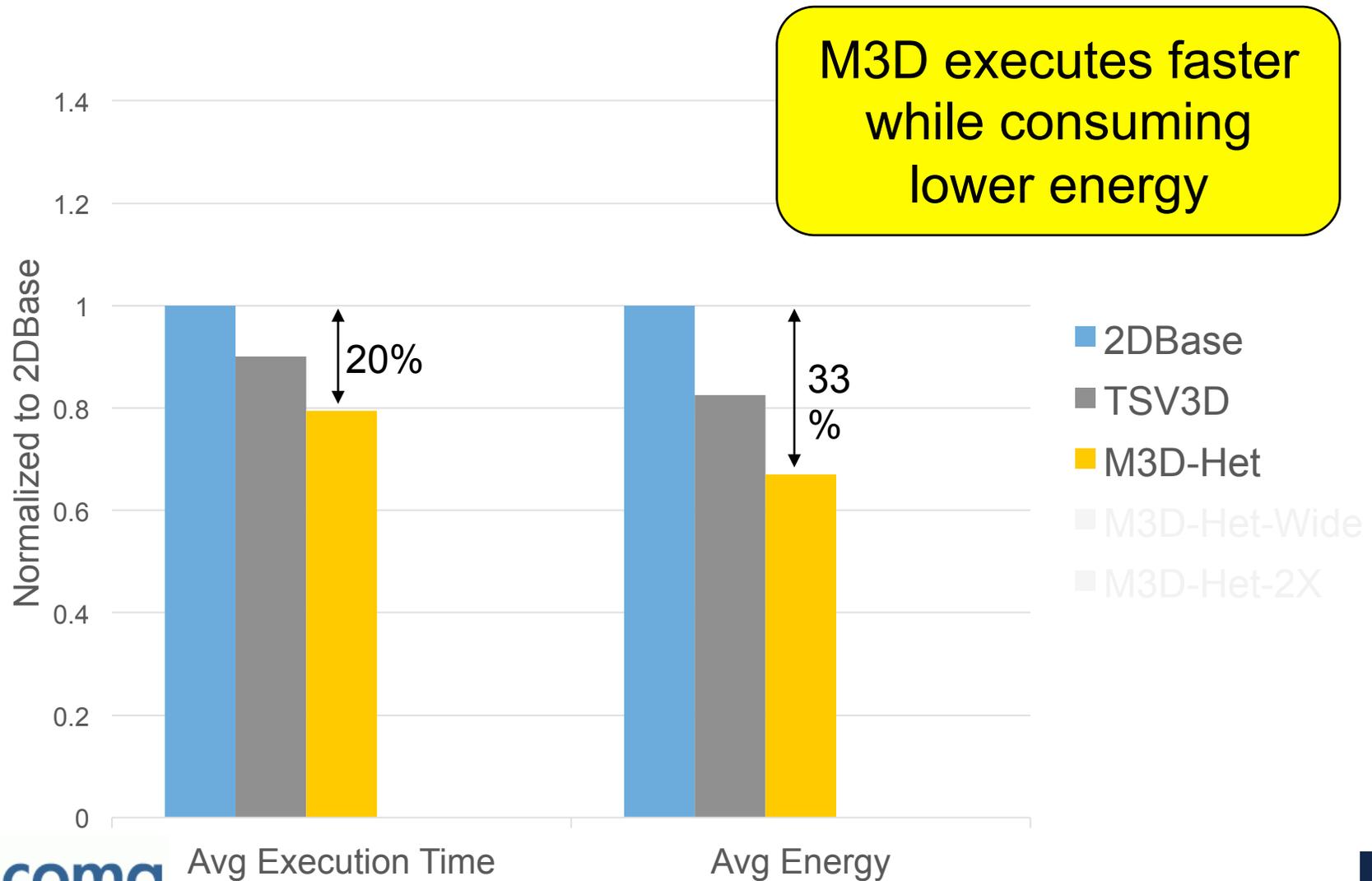
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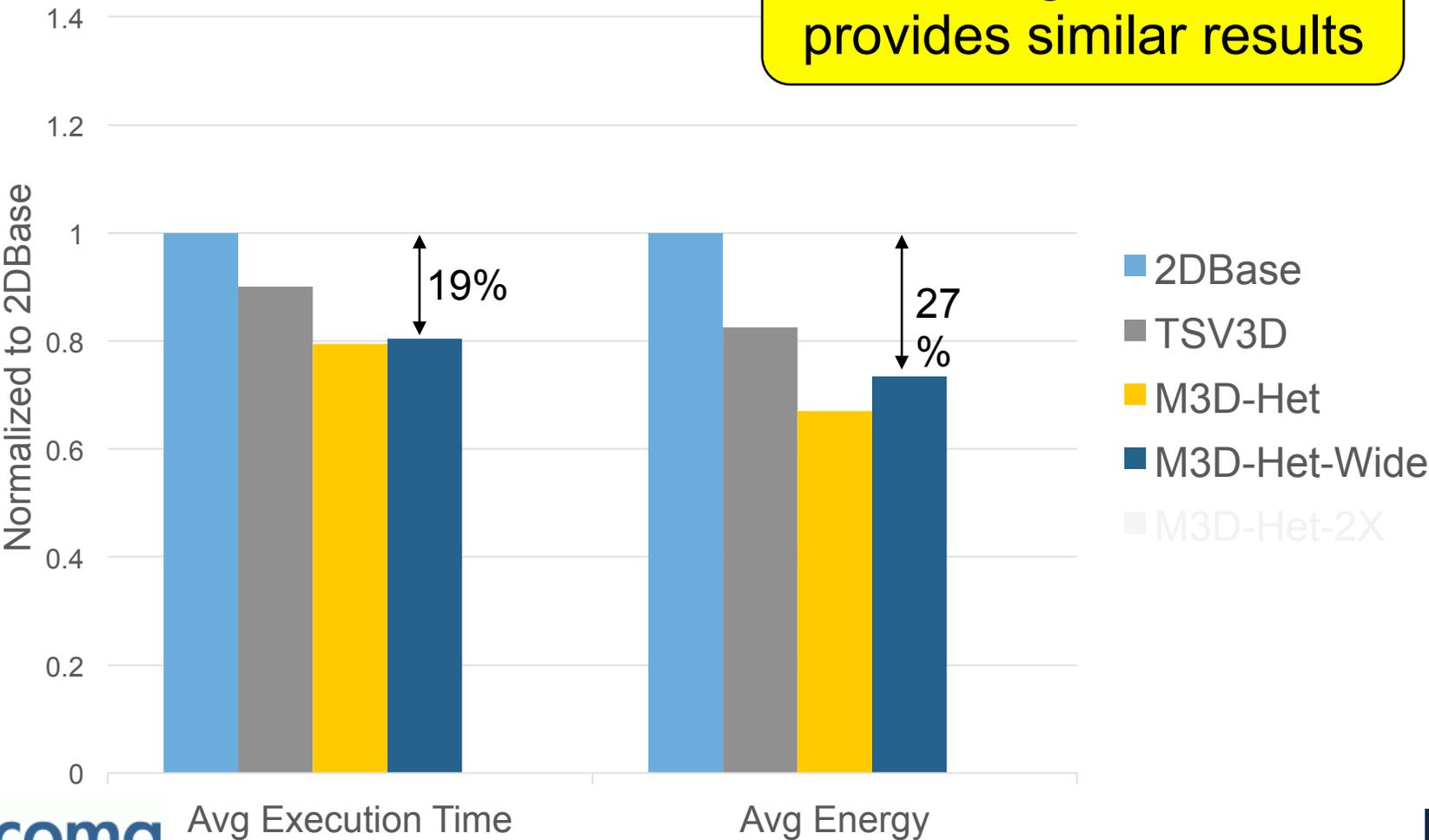


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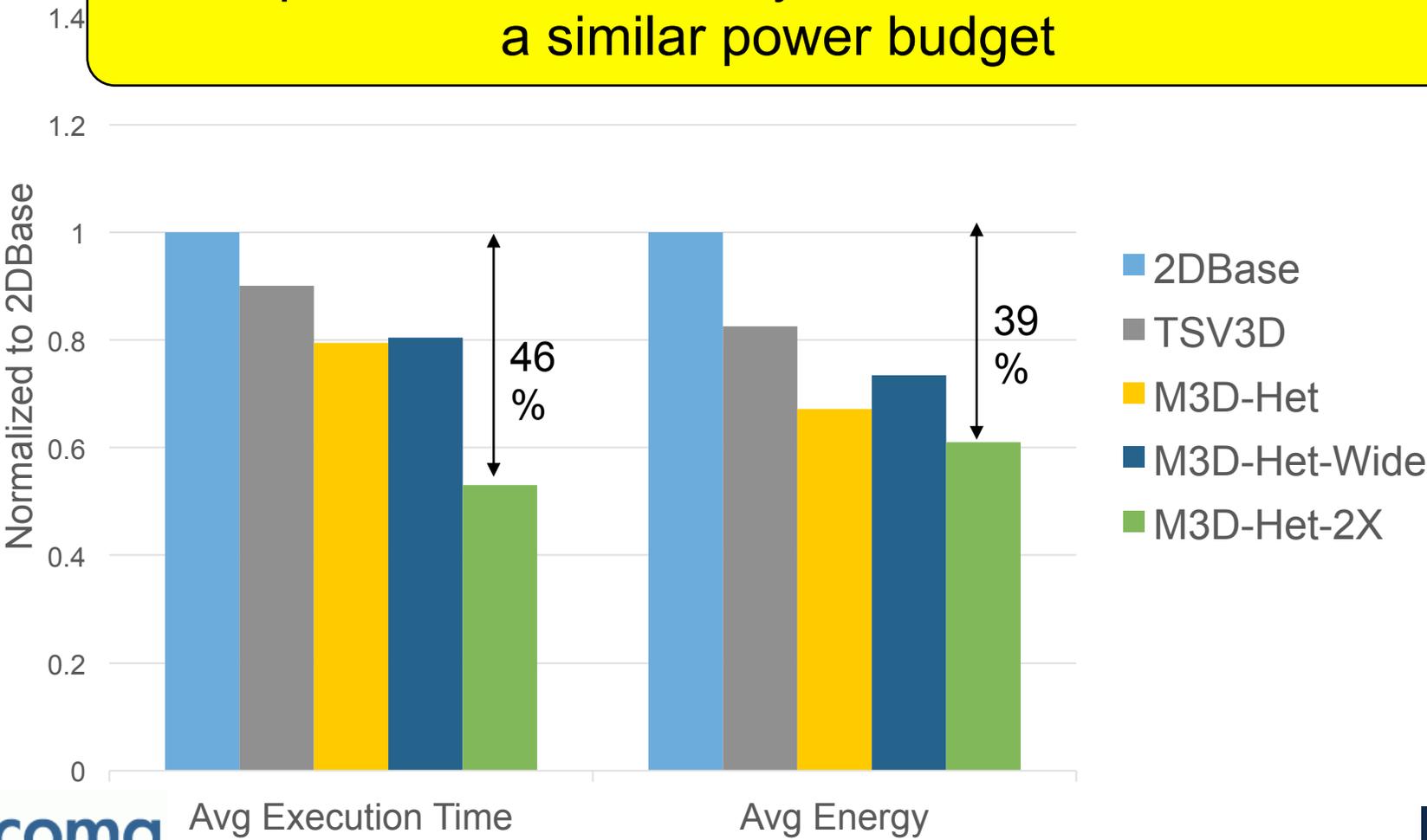
Evaluation of M3D Design Choices

Increasing issue width provides similar results



Evaluation of M3D Design Choices

Can operate twice as many M3D cores as 2DBase in a similar power budget



Monolithic 3D Core -- Partitioning Storage Stages

- Storage structures i.e. SRAM/CAM delays are proportional to height and width of an array

$$Width = N_{\downarrow bits} * (BitcellWidth + K * (N_{\downarrow r} + N_{\downarrow w}))$$

$$Height = N_{\downarrow words} * (BitcellHeight + K * (N_{\downarrow r} + N_{\downarrow w}))$$

$$Area = Width * Height \propto (N_{\downarrow r} + N_{\downarrow w})^2$$

Area of multiported cell is quadratic on the number of ports

